

In the specification

Amend the specification as follows:

Amend the paragraph beginning at page 11, line 7 as follows:

An example of a lithography process using a mask made in accordance with the present invention is shown in Fig. 2. Radiation comprising energy beam 30 passes through a portion of mask 18 comprising a substrate layer 20 sufficiently transparent to the radiation on which are deposited opaque segments conforming to the target image to be projected. Opaque segments 16 comprise a ~~the~~-parallel array of elements and form a portion of the total target portion of the lithography mask. The beam 30 portion that passes through the mask 18 between opaque segments 16 is illustrated by beam 30a. Beam 30a is focused by lens system 24 onto the surface 32 of a semiconductor wafer having conventional resist materials sensitive to the radiation. Radiation blocked by mask portions 16 does not transfer to the resist layer on surface 32. Thus, a contrasting latent image of the parallel array elements 16a is formed on wafer resist surface 32 which conforms to the pattern of the opaque layer on the mask. The resist is then developed, and the resist pattern created by the latent image is used to etch a desired target or portion thereof on the wafer. The target of the present invention is employed to determine the quality of the lithographic formation of functional circuits elsewhere on the wafer.

Amend the paragraph beginning at page 12, line 11 as follows:

The second, primarily dose sensitive mask portion 14 comprises an array of elements which includes a central element having a length in the vertical direction and a

width in the horizontal direction. On each side of central element 38 are a plurality of spaced, substantially parallel outer elements 40a, 40b, 42a, 42b, 44a, 44b, also having a length in the vertical direction and a width in the horizontal direction. The width of each of the outer elements is less than the width of the central element, and decreases with increasing distance of each outer element from the central element. As shown, on the right side of central element 38, the width of element 42a is less than the width of element 40a, and the width of element 44a is less than the width of element 42a. Likewise, on the left of the central element, the width of element 42b is less than the width of element 40b, and the width of element 44b is less than the width of element 42b. Other outer elements may be added as desired, however, the dose sensitive target is useful with even a single outer element spaced from and adjacent to a central element. The edges of outer elements 44a, 44b on each side of and farthest from central element 38 form opposing array edges. The sum of the width of each outer element and the spacing which separates the outer element from another element is the outer element pitch P_2 . To ensure that the outer elements are not resolved, P_2 is kept constant with increasing distance of each outer element from the central element. Alternatively, the width of the elements 40a, 40b, 42a, 42b, 44a, 44b could be kept constant while P_2 decreases; however, this would be a more difficult pattern to fabricate.